## 256K/512K bit Serial I<sup>2</sup>C bus EEPROM

## DESCRIPTION

The CW24C256B / 512B provides 262144 / 524288 bits of serial electrically erasable and programmable read-only memory (EEPROM), organized as 32768 / 65536 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The CW24C256B/512B is accessed via a two-wire serial interface and is available in 1.7V (1.7V to 5.5V) version.

## FEATURES

- Wide Voltage Operation V<sub>CC</sub> = 1.7V to 5.5V
- Operating Ambient Temperature: -40°C to +85°C
- Internally Organized:
  - CW24C256B, 32768 × 8 (256K bits)
  - CW24C512B, 65536 × 8 (512K bits)
- Two-wire Serial Interface
- Schmitt Trigger, Filtered Inputs for Noise Suppression
- Bidirectional Data Transfer Protocol
- Write Protect Pin for Hardware Data Protection
- 64-byte Page (CW24C256B),
  128-byte Page (CW24C512B) Write Modes
- Partial Page Writes Allowed
- Self-timed Write Cycle (5 ms max)
- High-reliability
  - Endurance: More than 5 Million Write Cycles
  - Data Retention: More than 200-years
- PDIP8/SOP8/TSSOP8/UDFN8/SOT23-5/ TSOT23-5/MSOP8 Packages

## **APPLICATIONS**

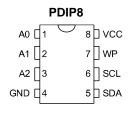
- Intelligent Instrument
- Household Appliance
- Automotive Electronics
- Computer/Notebook

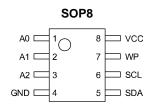


July. 2023

Rev 2.00

### **PIN CONFIGURATION**





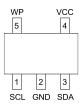
#### TSSOP8

A0 - 1	8 VCC
A1 🔤 2	7 🚞 WP
A2 🖂 3	6 🚞 SCL
GND - 4	5 DA

#### UDFN8 (bottom view)

vcc	8	1	A0
WP	<b>D</b> 7	2	A1
SCL	6	3	A2
SDA	5	4 🗆	GND

#### SOT23-5 / TSOT23-5



#### MSOP8

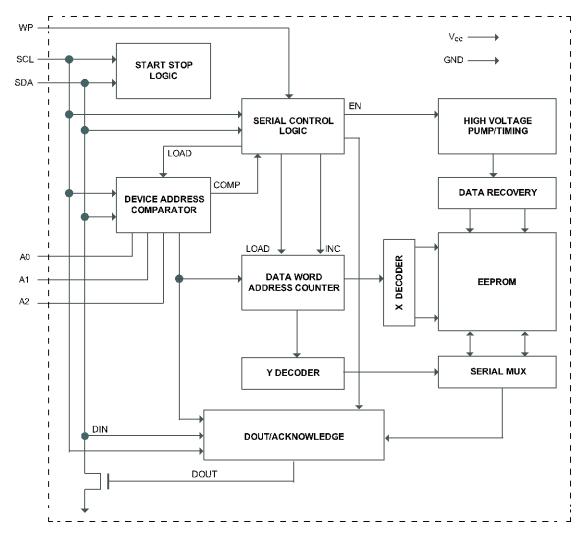
A0	1	8	
A1 A2	2 3	7 6	WP SCL
GND	4	5	SDA

## **ORDERING INFORMATION**

Temperature Range	Package		Orderable Device	Package Qty.
		PDIP8	CW24CXXXP	50 Units/Tube
		2000	CW24CXXXD	100 Units/Tube
		SOP8	CW24CXXXDR	3000 Units/R&T
	Pb-Free	TSSOP8	CW24CXXXT	100 Units/Tube
-40°C ~ +85°C			CW24CXXXTR	4000 Units/R&T
		UDFN8	CW24CXXXUR	4000 Units/R&T
		SOT23-5	CW24CXXXS5R	3000 Units/R&T
		TSOT23-5	CW24CXXXTS5R	3000 Units/R&T
		MSOP8	CW24CXXXM	4000 Units/R&T

XXX= 256B/512B

## **BLOCK DIAGRAM**





## **ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
DC Supply Voltage	V <sub>cc</sub>	-0.3 to + 6.5	V
DC Input Voltage	V <sub>IN</sub>	GND - 0.3 to $V_{CC}$ + 0.3	V
DC Output Voltage	Vout	GND - 0.3 to V <sub>CC</sub> + 0.3	V
Operating Ambient Temperature	Ta	-55 ~ +125	°C
Storage Temperature	T <sub>STG</sub>	-65 ~ +150	°C

(Maximum Ratings are those values beyond which damage to the device may occur.)

## **RECOMMENDED OPERATING CONDITIONS**

(Functional operation should be restricted to the Recommended Operating Conditions.)

Parameter	Symbol	Min	Max	Unit
DC Supply Voltage	V <sub>cc</sub>	1.7	5.5	V
Operating Temperature	T <sub>A</sub>	-40	+85	°C

### CAPACITANCE

(Applicable over recommended operating range from  $T_A = 25^{\circ}C$ , f = 1.0 MHz,  $V_{CC} = +1.7V$ )

Parameter	Symbol	<b>Test Conditions</b>	Min	Max	Unit
Input/Output Capacitance (SDA)	C <sub>I/O</sub>	$V_{I/O} = 0V$	-	8	pF
Input Capacitance (A0, A1, A2, SCL)	C <sub>IN</sub>	$V_{IN} = 0V$	-	6	pF

## DC ELECTRICAL CHARACTERISTICS

(Applicable over recommended operating range from:  $T_A = -40$  °C to +85 °C,  $V_{CC} = +1.7$ V to +5.5V unless otherwise noted)

Parameter	Symbol	Tes	t Conditions	Min	Тур	Max	Unit
	V <sub>CC1</sub>	-	-		-	5.5	
Supply Voltage	V <sub>CC2</sub>	-		2.5	-	5.5	v
Supply Voltage	V <sub>CC3</sub>	-		2.7	-	5.5	V
	V <sub>CC4</sub>	-		4.5	-	5.5	
Supply Current			Read at 400kHz	-	0.4	1.0	mA
Supply Current	Icc	$V_{CC} = 5V$	Write at 400kHz	-	2.0	3.0	mA
		$V_{\text{IN}} = V_{\text{CC}}$	or GND, V <sub>CC</sub> =1.7V	-	0.6	1.0	μA
Standby Current		$V_{IN} = V_{CC}$ or GND, $V_{CC}=2.5V$			1.0	2.0	μA
Standby Current	I <sub>SB</sub>	$V_{IN} = V_{CC}$ or GND, $V_{CC}=2.7V$		-	1.0	2.0	μA
		$V_{IN} = V_{CC}$	$V_{\rm IN} = V_{\rm CC}$ or GND, $V_{\rm CC} = 5.0V$		2.0	5.0	μA
Input Leakage	1	$V_{IN} = V_{CC}$ or GND			0.10	2.0	
Current	ILI			-	0.10	3.0	μA
Output Leakage	I <sub>LO</sub>	$V_{OUT} = V_C$	<sub>c</sub> or GND	-	0.05	3.0	μA



Current						
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
		$V_{CC} = 1.8V$ to 5.5V	-0.3	-	Vccx0.3	V
Input Low Level	V <sub>IL</sub>	V <sub>CC</sub> = 1.7V	-0.3	-	V <sub>CC</sub> x0.2	V
Input High Level	V <sub>IH</sub>	$V_{CC} = 1.7V$ to 5.5V	Vccx0.7	-	Vcc+0.3	V
Output Low	V <sub>OL3</sub>	$V_{CC} = 5.0V, I_{OL} = 3.0 \text{ mA}$	-	-	0.4	V
Output Low V <sub>OL2</sub>		$V_{CC} = 3.0V, I_{OL} = 2.1 \text{ mA}$	-	-	0.4	V
Level	V <sub>OL1</sub>	$V_{CC} = 1.7V, I_{OL} = 0.15 \text{ mA}$	-	-	0.2	V

## AC ELECTRICAL CHARACTERISTICS

(Applicable over recommended operating range from  $T_{\text{A}}$  = -40°C to +85°C,  $V_{\text{CC}}$  = +1.7V to

+5.5V, C <sub>L</sub> =	1 TTL Gate	and 100 pF	unless	otherwise	noted)
10.0 V, OL -			unicoo.	0110110100	notoa)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Cleak Fraguenay, SCI	£	1.7V <v<sub>CC&lt;2.5V</v<sub>	-	-	400	kHz
Clock Frequency, SCL	f <sub>SCL</sub>	2.5V <v<sub>CC&lt;5.5V</v<sub>	-	-	1000	КПZ
Clock Pulse Width Low	<b>t</b>	1.7V <v<sub>CC&lt;2.5V</v<sub>	1.2	-	-	110
Clock Pulse Width Low	t <sub>LOW</sub>	2.5V <v<sub>CC&lt;5.5V</v<sub>	0.6	-	-	μs
Clock Pulso Width High	t	1.7V <v<sub>CC&lt;2.5V</v<sub>	0.6	-	-	
Clock Pulse Width High	t <sub>HIGH</sub>	$2.5V < V_{CC} < 5.5V$	0.4	-	-	μs
Noise Suppression Time	tı	1.7V <v<sub>CC&lt;2.5V</v<sub>	-	-	50	nc
	ų	2.5V <v<sub>CC&lt;5.5V</v<sub>	-	-	50	ns
Clock Low to Data Out Valid	<b>+</b>	1.7V <v<sub>CC&lt;2.5V</v<sub>	0.1	-	0.9	
Clock Low to Data Out Valid	t <sub>AA</sub>	2.5V <v<sub>CC&lt;5.5V</v<sub>	0.05	-	0.9	μs
Time the bus must be free		1.7V <v<sub>CC&lt;2.5V</v<sub>	1.2	-	-	
before a new transmission can start	t <sub>BUF</sub>	2.5V <v<sub>CC&lt;5.5V</v<sub>	0.5	-	-	μs
Start Hold Time	t <sub>HD.STA</sub>	1.7V <v<sub>CC&lt;2.5V</v<sub>	0.6	-	-	
Start Hold Time		2.5V <v<sub>CC&lt;5.5V</v<sub>	0.25	-	-	μs
Start Satur Time	+	1.7V <v<sub>CC&lt;2.5V</v<sub>	0.6	-	-	
Start Setup Time	t <sub>su.sta</sub>	2.5V <v<sub>CC&lt;5.5V</v<sub>	0.25			μs
Data In Hold Time	t <sub>HD.DAT</sub>	1.7V <v<sub>CC&lt;5.5V</v<sub>	0	-	-	μs
Data In Setup Time	t <sub>su.dat</sub>	1.7V <v<sub>CC&lt;5.5V</v<sub>	100	-	-	ns
Inputs Rise Time	t <sub>R</sub>	-	-	-	300	ns
Inputs Fall Time	t <sub>F</sub>	-	-	-	300	ns
Stop Sotup Time	t	1.7V <v<sub>CC&lt;2.5V</v<sub>	0.6	-	-	110
Stop Setup Time	t <sub>su.sto</sub>	2.5V <v<sub>CC&lt;5.5V</v<sub>	0.25	-	-	μs
Data Out Hold Time	t <sub>DH</sub>	-	50	-	-	ns
Write Cycle Time	t <sub>WR</sub>	-	-	3.3	5	ms
5.0V,25°C,Byte Mode	Endurance		5M	-	-	Write



			Cycles

#### Note:

- 1. This parameter is characterized and is not 100% tested.
- 2. AC measurement condition :

Input pulse voltages: 0.3  $V_{CC}$  to 0.7  $V_{CC}$ ;

Input rise and fall time: 50 ns

Input and output timing reference voltages: 0.5  $V_{\text{CC}}$ 

The value of  $R_L$  should be concerned according to the actual loading on the user's system.

 $R_L$   $\ \ (connects to V_{CC}): 1.3 K\Omega \quad (2.5 V, 5 V)$  ,  $10 K\Omega \quad (1.7 V)$ 

### **PIN DESCRIPTION**

Ν	0.	Nomo	Eurotian Deparintian
5PIN	8PIN	Name	Function Description
-	1	A0	Address input. The A2, A1 and A0 pins are device address inputs for
-	2	A1	hard wire addressing and a total of eight CW24C256B/512B devices may be addressed on a single bus system (device addressing is
-	3	A2	discussed in detail under the Device Addressing section).
2	5	SDA	Serial address and data I/O. This pin is open-drain driven and may be wire- ORed with any number of other open-drain or open- collector devices.
3	6	SCL	Serial clock input. The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.
1	7	WP	Write protect. The WP pin that provides hardware data protection. The WP pin allows normal read/write operations when connected to ground (GND). When the WP pin is connected to $V_{CC}$ , the write protection feature is enabled and read only.
5	4	GND	Circuit ground pin.
4	8	VCC	Positive supply voltage.

### **MEMORY ORGANIZATION**

Device	Total bits	Total pages	Bytes per page	Word address
CW24C256B	256K	512	64	15-bit
CW24C512B	512K	512	128	16-bit

### **DEVICE OPERAN**

#### **Clock and data transitions**

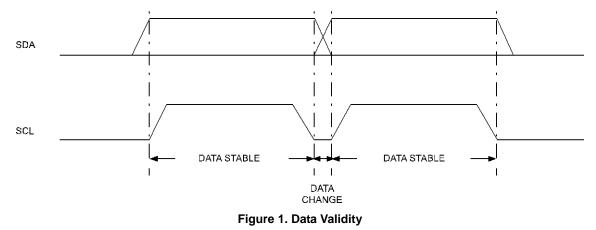
The SDA pin is normally pulled high with an external device. Data on the SDA pin may change



July. 2023

Rev 2.00

only during SCL low time periods (see Figure 1). Data changes during SCL high periods will indicate a start or stop condition as defined below.

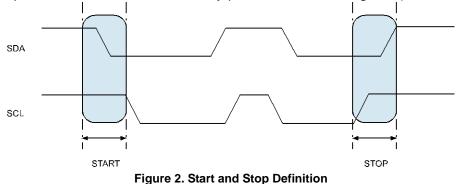


#### Start Conditions

A high-to-low transition of SDA with SCL high is a start condition which must precede any other Command. (see Figure 2)

#### **Stop Conditions**

A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode. (see Figure 2)



#### Acknowledge

All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a "0" to acknowledge that it has received each word. This happens during the ninth clock cycle.

#### Standby Mode

The CW24C256B/512B features a low-power standby mode which is enabled: (1) upon power-up and (2) after the receipt of the STOP bit and the completion of any internal operations.

### Memory Reset

After an interruption in protocol, power loss or system reset, any two-wire part can be reset by following these steps:

(1) Clock up to 9 cycles.



July. 2023

Rev 2.00

- (2) Look for SDA high in each cycle while SCL is high.
- (3) Create a start condition.

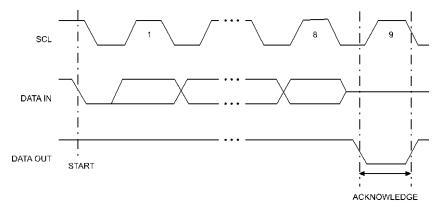


Figure 3. Output Acknowledge

## DEVICE ADDRESSING

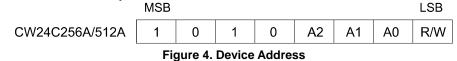
The CW24C256B/512B EEPROM devices all require an 8-bit device address word following a start condition to enable the chip for a read or write operation (see Figure 4)

The device address word consists of a mandatory "1", "0" sequence for the first four most significant bits as shown. This is common to all the Serial EEPROM devices.

The CW24C256B/512B EEPROM uses A2, A1 and A0 device address bits to allow as much as eight devices on the same bus. These 3 bits must be compared to their corresponding hardwired input pins. The A2, A1 and A0 pins use an internal proprietary circuit that biases them to a logic low condition if the pins are allowed to float.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a "0". If a compare is not made, the chip will return to a standby state.



### **Data Security**

The CW24C256B/512B has a hardware data protection scheme that allows the user to write protect the entire memory when the WP pin is at VCC.

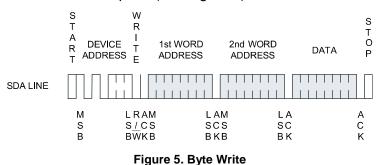
## WRITE OPERATIONS

### **Byte Write**

A write operation requires an 8-bit data word address following the device address word and



acknowledgment. Upon receipt of this address, the EEPROM will again respond with a "0" and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a "0" and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally timed write cycle,  $t_{WR}$ , to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see Figure 5).

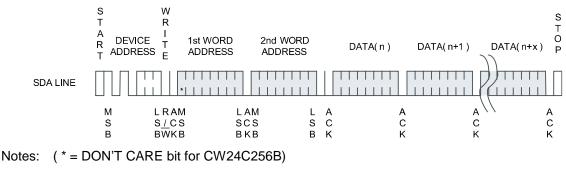


#### Page Write

The CW24C256B is capable of 64-byte page write. The CW24C512B is capable of 128-byte page write.

A page write is initiated the same as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to 63 (CW24C256B) or 127 (CW24C512B) more data words. The EEPROM will respond with a "0" after each data word received. The microcontroller must terminate the page write sequence with a stop condition (see Figure 6).

The data word address lower 6 (CW24C256B) or 7 (CW24C512B) bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than 32 (CW24C256B) or 128 (CW24C512B) data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten.



#### Figure 6. Page Write

#### Acknowledge Polling

Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the



device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a "0", allowing the read or write sequence to continue.

## READ OPERATIONS

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to "1". There are three read operations: current address read, random address read and sequential read.

### **Current Address Read**

The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page.

Once the device address with the read/write select bit set to "1" is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input "0" but does generate a following stop condition (see Figure 7).

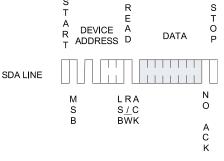


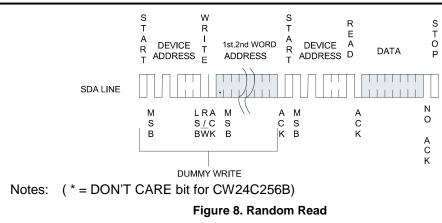
Figure 7. Current Address Read

### Random Read

A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a "0" but does generate a following stop condition (see Figure 8).



9



#### Sequential Read

Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledgement. As long as the EEPROM receives an acknowledgement, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a "0" but does generate a following stop condition (see Figure 9).

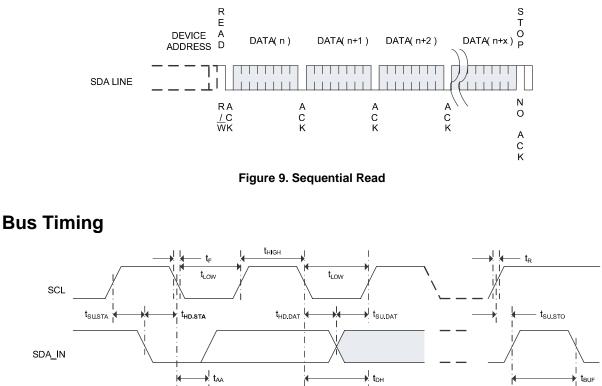
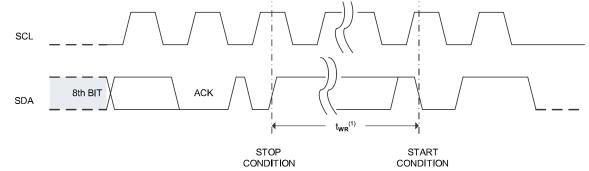


Figure 10. SCL: Serial Clock, SDA: Serial Data



SDA\_OUT

## Write Cycle Timing

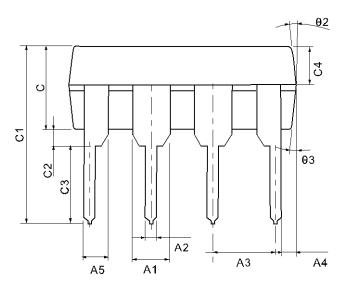


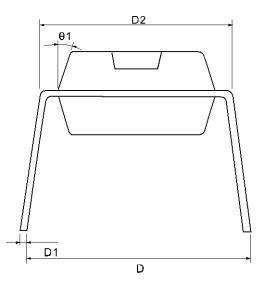
Notes: The write cycle time  $t_{WR}$  is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

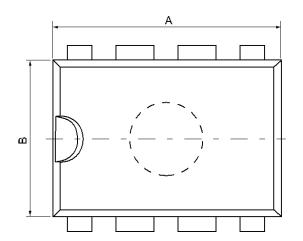
Figure 11. SCL: Serial Clock, SDA: Serial Data I/O

## PHYSICAL DIMENSIONS

DIP8







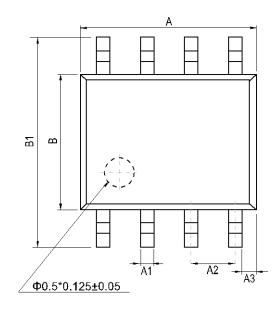


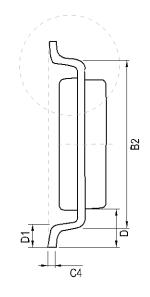
July. 2023

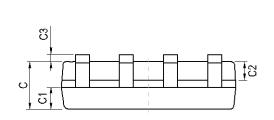
Rev 2.00

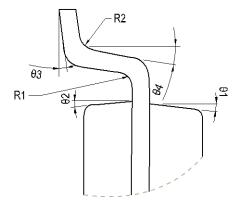
Symbol	Dimensio	on (mm)	Symbol	Dimensio	n (mm)
Symbol	Min	Max	Symbol	Min	Max
А	9.00	9.20	C2	0.50 (	TYP)
A1	1.474	1.574	C3	3.20	3.40
A2	0.41	0.51	C4	1.47	1.57
A3	2.44	2.64	D	8.20	8.80
A4	0.51 (	TYP)	D1	0.244	0.264
A5	0.99 (	TYP)	D2	7.62	7.87
В	6.10	6.30	θ1	17° (TYP)	
С	3.20	3.40	θ2	10° (TYP)	
C1	7.10	7.30	θ3	8° (TYP)	

### SOP8









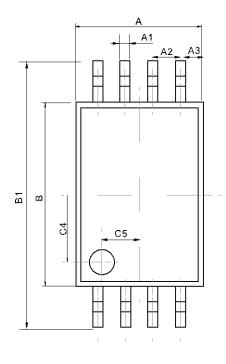
Sum	ahal	Dimension (mm)		Symbol	Dimension (mm)	
Syn	nbol	Min	Max	Symbol	Min	Max
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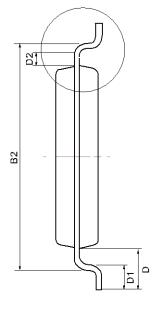
Rev 2.00

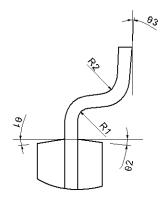
www.whxy.com

A	4.80	5.00	C3	0.05	0.20
A1	0.356	0.456	C4	0.203	0.233
A2	1.27 (	TYP)	D	1.05 (	TYP)
A3	0.345	(TYP)	D1	0.40 0.80	
В	3.80	4.00	R1	0.20 (TYP)	
B1	5.80	6.20	R2	0.20	TYP)
B2	5.00 (	TYP)	θ1	17° (	(PYP)
С	1.30	1.60	θ2	13° (TYP)	
C1	0.55	0.65	θ3	0° ~ 8° (TYP)	
C2	0.55	0.65	θ4	4° ~ 12° (TYP)	

### TSSOP8







Symbol	Dimensio	on (mm)	Symbol	Dimension (mm)	
Symbol	Min	Max	- Symbol	Min	Max
А	2.90	3.10	C4	1.55	1.65

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July. 2023

0 0

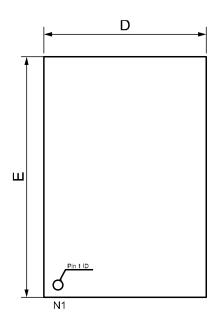
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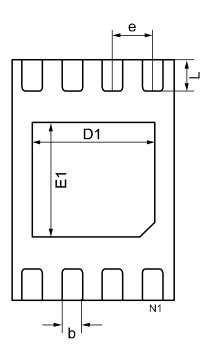
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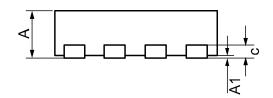
	-				
A1	0.20	0.30	C5	0.85	0.95
A2	0.60	0.70	D	1.00 (	TYP)
A3	0.41	0.42	D1	0.50	0.70
В	4.30	4.50	D2	0.19	0.29
B1	6.30	6.50	R1	0.15 (TYP)	
B2	5.404	5.504	R2	0.15 (	TYP)
С	0.95	1.05	θ1	12° (	TYP)
C1	0.415	0.465	θ2	12° (TYP)	
C2	0.39	0.49	θ3	0° ~ 7°	
C3	0.05	0.15	-	-	

UDFN8





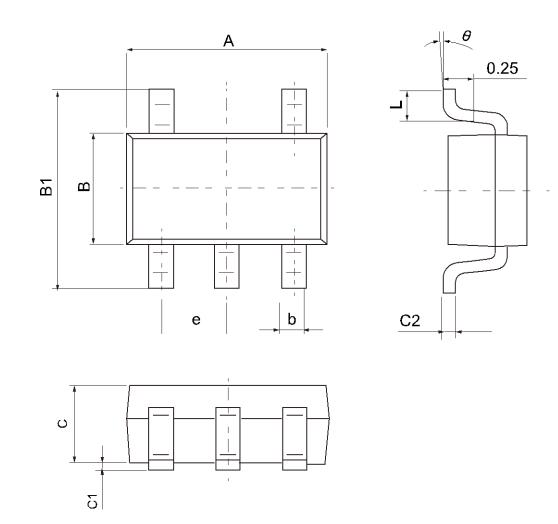
bottom view



Symbol	Dimension (mm)	Symbol	Dimension (mm)
Ju	ly. 2023		
	ev 2.00		www.whxy.com
		1.4	

	Min	Тур.	Max		Min	Тур.	Max
А	0.50	0.55	0.60	е	0.50TYP		
A1	0.00	0.03	0.05	E	2.95	3.00	3.05
b	0.20	0.25	0.30	E1	1.30	1.40	1.50
С	0.152REF			D1	1.40	1.50	1.60
D	1.95	2.00	2.05	L	0.35	0.40	0.45

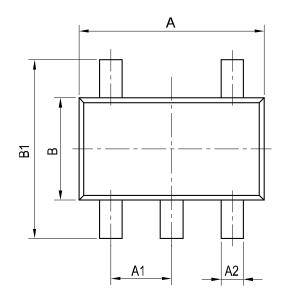
SOT23-5

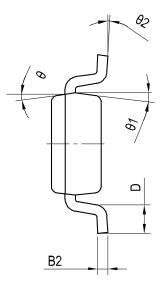


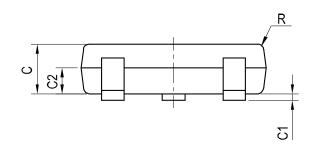
Symbol		Dimension (mm)		Symbol	Dimension (mm)	
		Min	Max	Symbol	Min	Max
	July. 20	23				
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А	2.82	3.02	С	1.05	1.15
е	0.95 (	BSC)	C1	0.03	0.15
b	0.28	0.45	C2	0.12	0.23
В	1.50	1.70	L	0.35	0.55
B1	2.75	3.05	θ	0°	8°

TSOT23-5



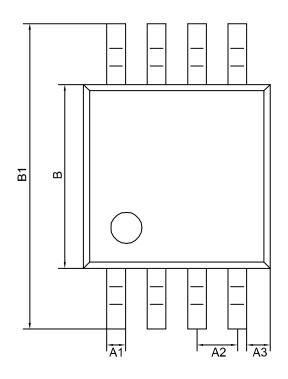


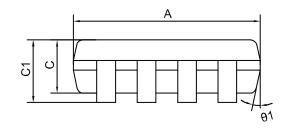


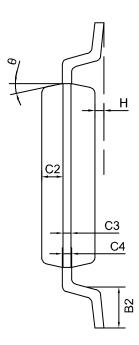
Symbol	Dimension (mm)		Symbol	Dimension (mm)	
Symbol	Min	Мах	Symbol	Min	Max
Jul	ly. 2023				
Re	v 2.00				www.whxy.com

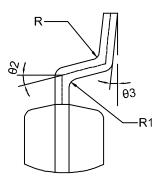
A	2.820	3.020	C1	0.000	0.100
A1	0.950 (BSC)		C2	0.378	0.438
A2	0.350	0.500	D	0.300	0.600
В	1.600	1.700	θ	9° TYP4	
B1	2.650	2.950	θ1	10° TYP4	
B2	0.080	0.200	θ2	0~8°	
С	0.700	0.800	-	-	

MSOP8











July. 2023 Rev 2.00

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Symbol	Dimension (mm)		Symphol	Dimension (mm)	
	Min	Max	Symbol	Min	Max
А	2.90	3.10	C3	0.152	
A1	0.28	0.35	C4	0.15	0.23
A2	0.65	TYP	Н	0.00 0.09	
A3	0.375TYP		θ	12° TYP4	
В	2.90	3.10	θ1	12° TYP4	
B1	4.70	5.10	θ2	14° TYP	
B2	0.45	0.75	θ3	0° ~ 6°	
С	0.75	0.95	R	0.15TYP	
C1	-	1.10	R1	0.15TYP	
C2	0.328TYP		-	-	

